

/ Descriptions

VRW056 M M SQS æ M y s ll 1 Silicon PNP transistor in a SOT-23 Plastic Package.

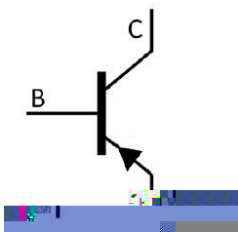
/ Features

⇒ я η / k_{IH} ħ 1 ó B

Low saturation voltage, excellent h_{FE} linearity and high h_{FE} .

$\tilde{\omega} \approx \frac{1}{\sqrt{2}} \left(\frac{1}{\sqrt{2}} + i \right) \Omega = \frac{1}{2} (1+i) \Omega$

Output stage of audio amplifier, voltage regulator, DC-DC converter and relay driver.



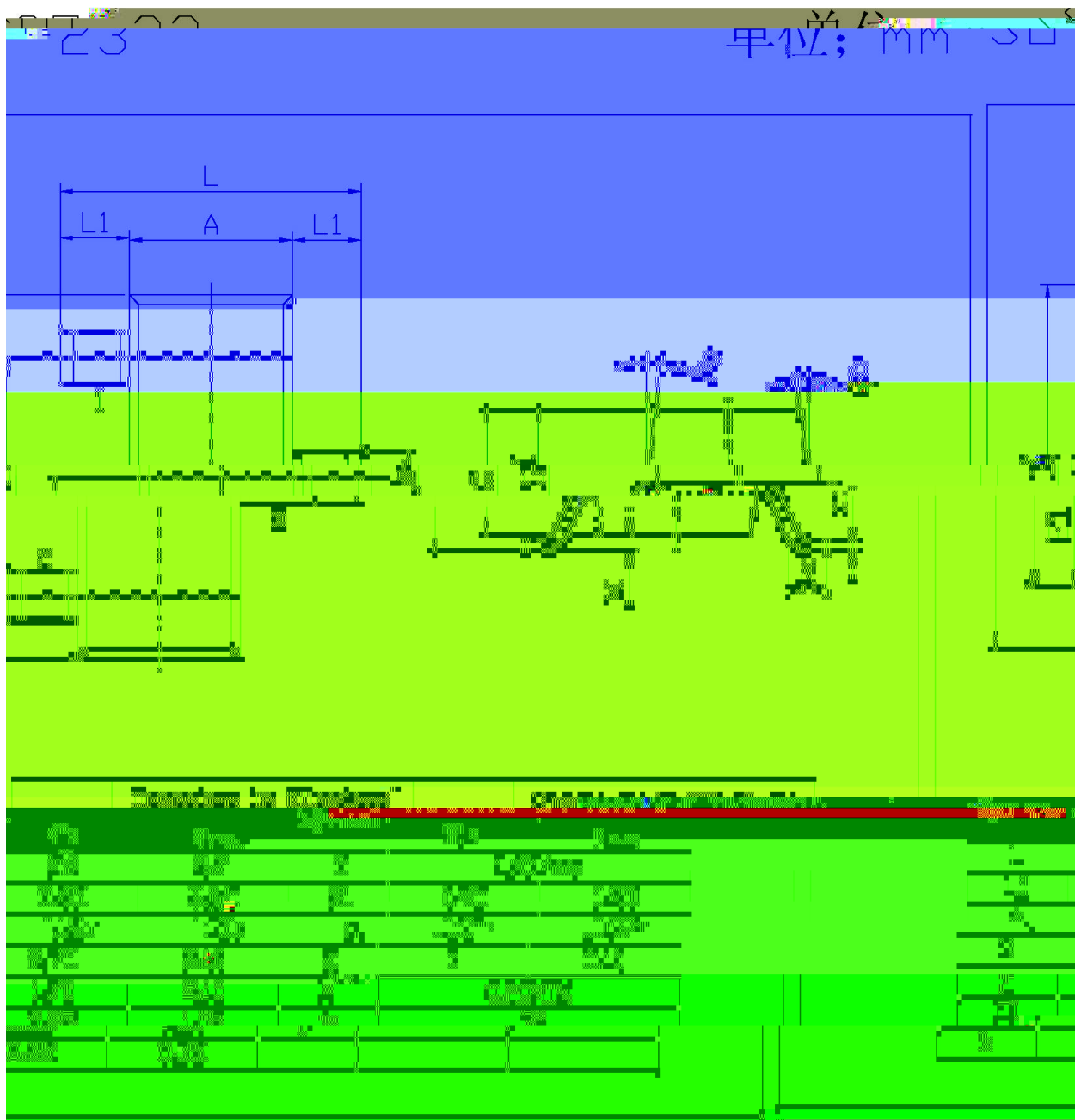
PIN1 $\times$ Base PIN 2 $\times$ Emitter PIN 3 $\times$ Collector

/ h_{FE} Classifications & Marking

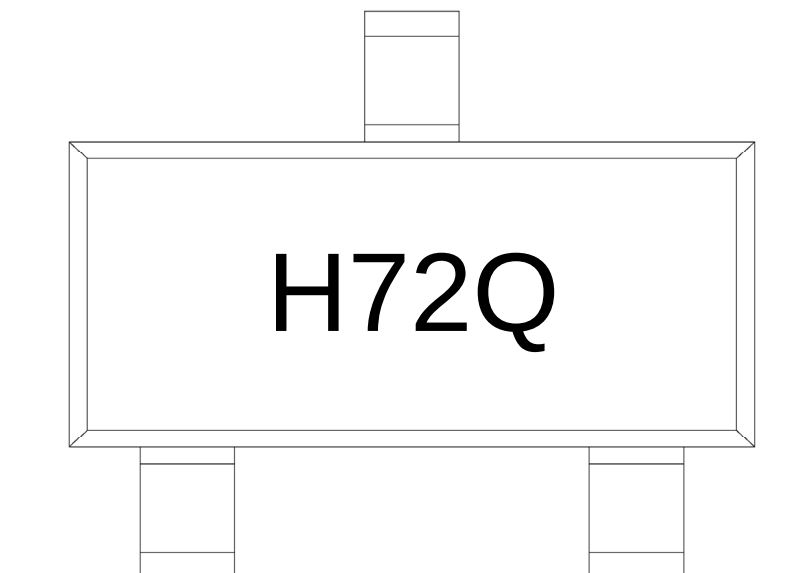
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - DC	I_C	-3	A
Collector Current - Pulse	I_{CP}	-7	A
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$ $I_C = 0$	-5			V

/ Package Dimensions



/ Marking Instructions



" X

K X ㄣ 3 1 ㄩ

:5 X ㄣ 3 N ㄩ

T X ㄣ 6 ㄥ ㄩ

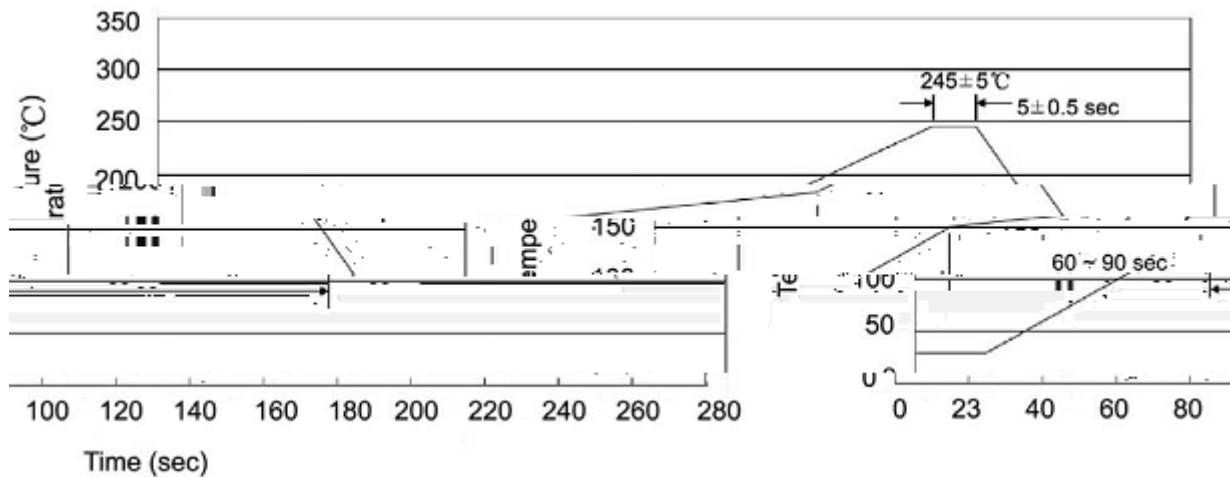
Note:

H: Company Code

72: Product Type Code

Q: h_{FE} Classifications Symbol Code

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



1. Preheating: 25~150 °C, Time: 60~90sec;
2. Peak Temp.: 245±5 °C, Duration: 5±0.5sec;
3. Cooling Speed: 2~10 °C/sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 245±5 °C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ 260±5 °C, Time: 10±1 sec. Temp.: 260±5 °C Time: 10±1 sec

/ Packaging SPEC.

□ / REEL

Package Type	Units					Dimension (unit: mm)		
						ρ		

/ Notices